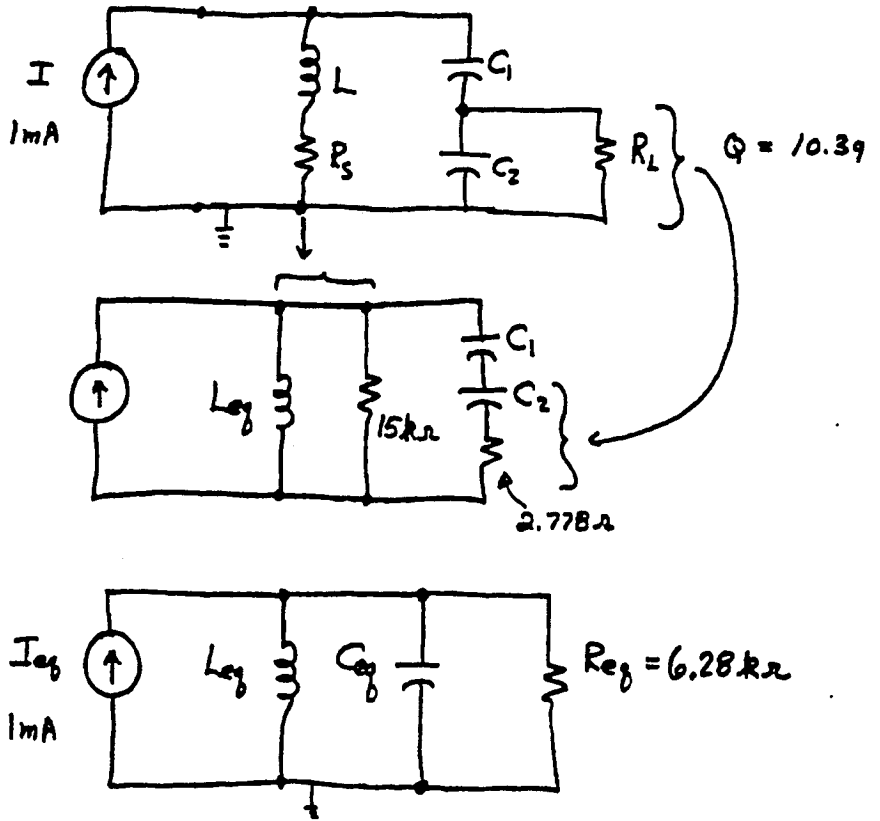


Problem 11.33

Let us assume that high-Q approximations are valid. Then $L_{eq} = L = 0.5 \mu\text{H}$ and $C_{eq} = 1/(1/C_1 + 1/C_2) = 16.67 \text{ pF}$. Also we have $f_0 = \left[2\pi\sqrt{L_{eq}C_{eq}}\right]^{-1} = 55.133 \text{ MHz}$.

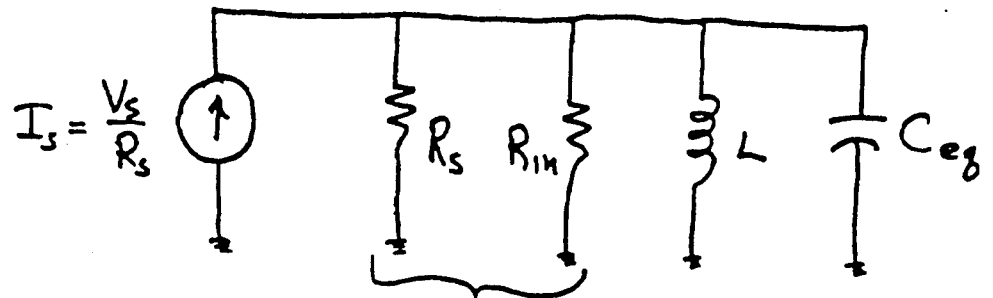


A simulation comparing the voltage across the current source in the original circuit with that of the equivalent circuit is stored in the file named P11_33.

Problem 11.37

$$Q = f_0/B = (10 \text{ MHz})/(100 \text{ kHz}) = 100$$

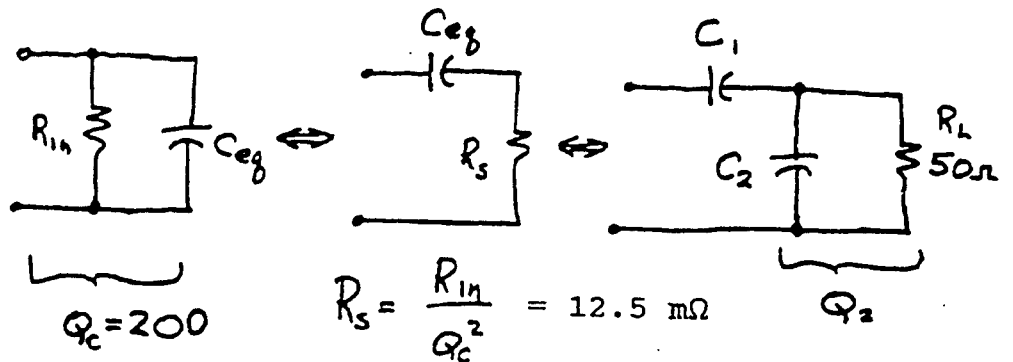
The parallel equivalent circuit is:



$$R_{eq} = R_s \parallel R_{in} = 250 \Omega$$

$$L = R_{eq}/(Q\omega_0) = 39.8 \text{ nH}$$

$$C_{eq} = \frac{1}{\omega_0^2 L} = 6364 \text{ pF}$$



$$Q_2^2 = R_L/R_s = 63.24 = \omega_0^2 C_2 R_L \Rightarrow C_2 = 20.13 \text{ nF}$$

$$C_{eq} = \frac{1}{1/C_1 + 1/C_2} \Rightarrow C_1 = 9.305 \text{ nF}$$

The simulation file is P11_37.

11.44

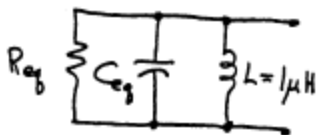
$$(a) K = I_{DSS}/V_{to}^2 = (4 \times 10^{-3})/(-2)^2 = 1 \text{ mA/V}^2$$

$$I_{DQ} = K(V_{GSQ} - V_{to})^2 \Rightarrow V_{GSQ} = -0.585 \text{ V}$$

$$R_{S1} = R_{S2} = (15 + 0.585)/I_{DQ} = 7.79 \text{ k}\Omega$$

Thus we choose the standard value $R_{S1} = R_{S2} = 8.2 \text{ k}\Omega$.

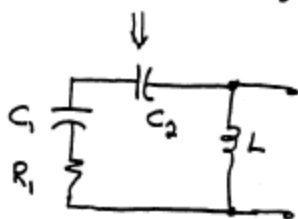
(b)



$$Q = f_0/B = (10 \text{ MHz})/(500 \text{ kHz}) = 20$$

$$C_{eq} = 1/\omega_0^2 L = 253.3 \text{ pF}$$

$$R_{eq} = Q\omega_0 L = 1257 \Omega$$



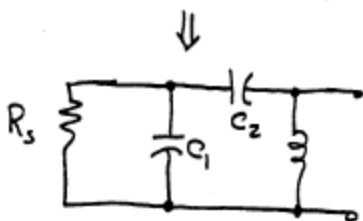
$$R_1 = R_{eq}/Q^2 = 3.142 \Omega$$

$$Q_1 = 1/\omega_0 C_1 R_1 = \sqrt{R_S/R_1} = 3.99$$

$$C_1 = 1269 \text{ pF}$$

$$C_{eq} = \frac{1}{1/C_1 + 1/C_2}$$

$$C_2 = 316.43 \text{ pF}$$



(c) This part is very similar to part (b). The results are $C_3 = 256.51 \text{ pF}$ and $C_4 = 20.21 \text{ nF}$.

(d) First we compute g_m for the transistors.

$$g_m = \frac{2\sqrt{I_{DSS} I_{DQ}}}{|V_{to}|} = 2.83 \text{ mS}$$

The voltage gain at resonance is the product of three terms:

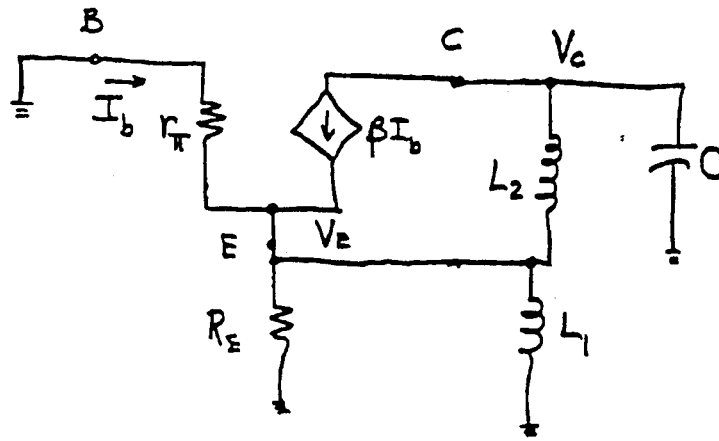
- (1) voltage step up in the input circuit
- (2) voltage gain of the differential pair
- (3) voltage step down in the output circuit

Factors 1 and 3 offset one another and the voltage gain is

$$A_V = g_m R_{eq}/2 = 1.78$$

PROBLEM 11.14

(a)



(b) Write node voltage equations:

$$\frac{V_E}{r_{\pi}} + \beta \frac{V_E}{r_{\pi}} + \frac{V_E}{R_E} + \frac{V_E}{j\omega L_1} + \frac{V_E - V_C}{j\omega L_2} = 0$$

$$-\beta \frac{V_E}{r_{\pi}} + \frac{V_C - V_E}{j\omega L_2} + j\omega C V_C = 0$$

$$\begin{vmatrix} \frac{1}{R_E} + \frac{\beta+1}{r_{\pi}} + \frac{1}{j\omega L_1} + \frac{1}{j\omega L_2} & -\frac{1}{j\omega L_2} \\ -\frac{\beta}{r_{\pi}} - \frac{1}{j\omega L_2} & j\omega C + \frac{1}{j\omega L_2} \end{vmatrix} = 0$$

Eventually we have:

$$\omega = \frac{1}{\sqrt{C(L_1 + L_2)}} \quad \beta_{\min} = \frac{L_1}{L_2} \left(1 + \frac{r_{\pi}}{R_E} \right)$$

(c) Design for $\beta_{\min} = 50$

$$R_E \approx \frac{V_{EE} - V_{BEQ}}{I_{CQ}} = 15 \text{ k}\Omega$$

$$r_{\pi} = \frac{\beta V_T}{I_{CQ}} = \frac{50 (26 \text{ mV})}{1 \text{ mA}} = 1300 \Omega$$

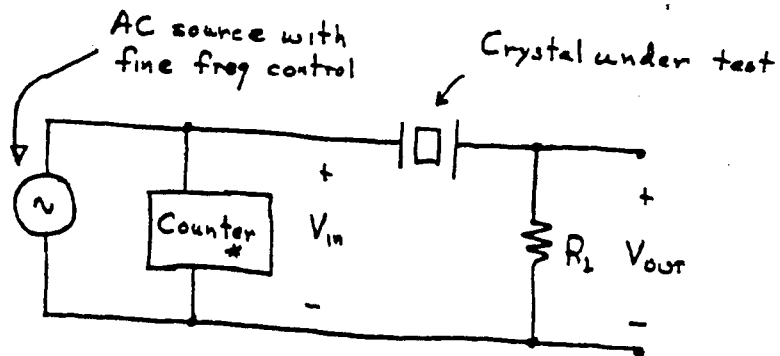
Choose $C = 270 \text{ pF}$

$$\left. \begin{aligned} L_1 + L_2 &= \frac{1}{\omega^2 C} = 93.8 \mu\text{H} \\ \frac{L_1}{L_2} &= \frac{\beta_{\min}}{1 + r_{\pi}/R_E} = 46 \end{aligned} \right\} \Rightarrow \begin{aligned} L_1 &= 91.8 \mu\text{H} \\ L_2 &= 2 \mu\text{H} \end{aligned}$$

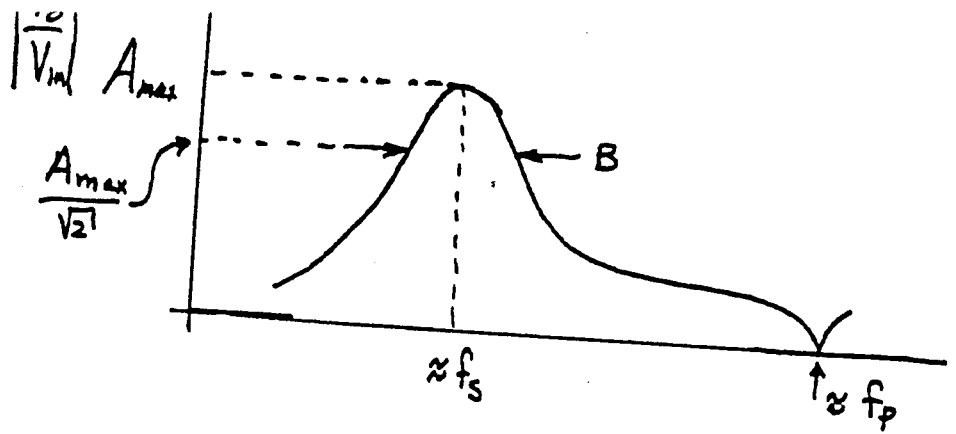
We selected $C_C = 0.01 \mu\text{F}$ so it appears as nearly a short c at the frequency of oscillation.

Problem 11.59

(a) Set up the system shown below.



Use the counter to accurately measure the frequency of the source. Choose $R_L \approx R_S$ of the crystal. Start with about 50Ω and adjust as needed. Observe the voltage transfer function magnitude $|V_o/V_{in}|$ which will appear much like the sketch shown on the next page. From the plot, determine the peak A_{max} , f_s at which the transfer function peak occurs, the half-power bandwidth B of the peak, and f_p which is the frequency of the null.



Then the crystal parameters can be calculated:

$$A_{\max} = \frac{R_L}{R_S + R_L} \Rightarrow R_S = \frac{1 - A_{\max}}{A_{\max}} \times R_L$$

$$Q_{\text{circuit}} = \frac{f_s}{B} = \frac{\omega_s L_S}{R_S + R_L} = \frac{1}{\omega C_S (R_S + R_L)}$$

$$L_S = \frac{(R_S + R_L) Q_{\text{circuit}}}{\omega_s}$$

$$C_S = \frac{1}{\omega_s Q_{\text{circuit}} (R_S + R_L)}$$

$$Q = \frac{\omega_s L_S}{R_S}$$

(b) Given $f_s = 1.000000$ MHz, $f_p = 1.000500$ MHz, $R_S = 300 \Omega$
 $= 10,000$ we have:

$$L_S = R_S Q / \omega_s = 477.465 \text{ mH}$$

$$C_S = 1 / (Q \omega_s R_S) = 53.0516 \times 10^{-15} \text{ F}$$

Let $C_{\text{eq}} = \frac{1}{1/C_S + 1/C_P}$ denote the parallel equivalent capacitance. Then we have:

$$C_{\text{eq}} = \frac{1}{\omega_p^2 L_S}$$

$$= 52.9986 \times 10^{-15} \text{ F}$$

$$C_P = \frac{1}{1/C_{\text{eq}} - 1/C_S} = 53 \text{ pF}$$